

DESCRIPTION

WIRING MATERIAL AND WIRING BOARD USING THE SAME

5 TECHNICAL FIELD

The present invention relates to wiring materials and reflective electrodes for use in TFT liquid crystal displays (TFT-LCDs) or organic electroluminescence devices, and a manufacturing method thereof.

10

BACKGROUND ART

Thin-film transistor (TFT) liquid crystal displays (which are referred to simply as TFT-LCDs, hereinafter) have distinctive features, such as high display performance and superior energy efficiency, and have thus become mainstream displays used in portable personal computers, laptop computers, TVs, and other display systems. While different manufacturers offer different methods for producing TFT-LCDs, each method involves many steps and requires deposition of various metals and metal oxides. Thus, there is a need to reduce the number of production steps involved.

TFTs are also used to drive organic electroluminescence (EL) displays, another type of display devices.

Basic structure of TFT-LCDs

25 The basic structure of conventional TFT-LCDs is first

described. Referring to Fig. 3, a transmissive TFT-LCD is shown in a schematic cross-section. As shown, the transmissive TFT-LCD has a basic structure in which a liquid crystal 10 is sandwiched between a color filter substrate 12 and a TFT substrate 14. A backlight 16 is placed behind the TFT substrate 14 to illuminate the transmissive TFT-LCD from behind.

The color filter substrate 12 has a structure in which a color filter 22 is sandwiched between a glass substrate 18a and a transparent electrode 20. The color filter substrate 12 transmits red (R), green (G), and blue (B) light.

The TFT substrate 14 includes a transparent electrode 20b disposed on a glass substrate 18b. Signal voltages are applied to the transparent electrode 20 via a TFT 24.

In the construction shown in Fig. 3, a single polarizer is arranged on one face of the color filter substrate 12 and another polarizer on one face of the TFT substrate 14. Such a construction is well known in the art.

Unlike the transmissive TFT-LCD of Fig. 3, a reflective TFT-LCD has a construction in which the TFT substrate 14 includes, rather than the transparent electrode 20b, a reflective electrode made of aluminum or a similar reflective material. Since the reflective TFT-LCD reflects incoming light, it does not require the backlight 16.

Referring now to Fig. 4, the basic structure of a single

pixel on the TFT substrate 14 of the transmissive TFT-LCD is shown in a schematic plan view. As shown, data on a signal line 30 is applied to the transparent electrode 20b via switching by a TFT 24. The TFT 24 includes a source electrode 32, a gate electrode 34 and a drain electrode 36. An amorphous silicon 38 and other materials are deposited in the region of the gate electrode 34.

Referring to Fig. 5, which is a schematic cross-section taken along the line V-V' of Fig. 4, the gate electrode 34 is disposed on the glass substrate 18b and is overlaid with an SiN_x film 35. Also disposed above the gate electrode 34 is the layer of amorphous silicon 38.

The source electrode 32 and the drain electrode 36 are arranged on opposite ends of the amorphous silicone 38, each partially overlapping the gate electrode. These components are entirely overlaid with an insulation film 40. The transparent electrode 20b is disposed over the insulation film 40 and is electrically connected to the drain electrode 36 via a through hole 40b formed in the insulation film 40.

Wiring used in TFT-LCDs

In the production of TFT arrays for driving conventional TFT-LCDs, the possibility of using such metals as Cr, TaW, and MoW in the gate electrodes or the source/drain electrodes has been examined.

Of these metals, Cr is readily workable but is

susceptible to corrosion, whereas TaW and MoW are relatively resistant to corrosion but have a large electrical resistance.

Thus, workable metals with low electrical resistance have been widely used. When we simply say "metals with low electrical resistance," what comes first to mind are such metals as Ag, Cu, and Al. For this reason, TFT arrays (transistor arrays) using aluminum-based wiring have been proposed conventionally. It has been known that aluminum may cause formation of protrusions known as "hillocks" on the surface of electrodes. When formed on electrodes such as the source electrodes of a TFT, the hillocks may penetrate the overlaying insulation layer and come into contact with the top transparent electrode, resulting in defective products. Thus, Nd has been added to aluminum to prevent formation of such hillocks.

When such an aluminum electrode directly comes into contact with the silicon layer and the transparent electrode, however, aluminum may diffuse into the silicon layer, causing a decrease in the device performance or oxidation of aluminum into alumina, which quite likely results in an increase in the electrical resistance between the transparent electrode and the TFT. As a result, the components of the TFT array may fail.

The addition of Nd to aluminum may also lead to a high electrical resistance comparable to that of TaW and MoW.

For these reasons, one conventional, improved approach

employs a structure in which the aluminum electrode is sandwiched by Mo or Ti to minimize the contact resistance with the oxide-made transparent electrode. Specifically, Mo is first deposited over the silicon layer and the aluminum layer is then formed on top of the Mo film to prevent diffusion of aluminum into the silicon layer. Another Mo layer is then deposited over the aluminum layer to prevent the increase in the contact resistance with the transparent electrode due to oxidation. In brief, the conventional TFT-LCDs employ the three-layered wirings of Mo/Al/Mo. Three-layered wirings of Ti/Al/Ti are also employed for the same reason.

Conventional Examples of Ag Alloys

Japanese Patent No. 1297072 describes one example in which an Ag-based alloy is used as a material to form electrical contacts. The patent discloses the use of an Ag alloy containing 5 to 20wt% of one or two of Fe, Co, and Ni. Ag alloys of other compositions are also described. Also, Japanese Patent No. 1585932 describes an Ag alloy containing Ni and Zr in amounts of 5 to 25wt% and 0.05 to 8wt%, respectively.

Japanese Patent Laid-Open Publication No. 2001-192752 describes one example in which an Ag-based alloy is used as a metal material for various electronic parts. The Ag alloy described in this publication contains 0.1 to 3wt% of Pd along with total of 0.1 to 3wt% of Au, Pt, Cu, Ta, Cr, Ti, Ni, Co,

Si, or other metals.

Japanese Patent Laid-Open Publication No. 2001-102592 describes one example in which a particular Ag-based alloy is used in gate electrodes. Aside from Ag to serve as the major component, this alloy contains Pd and one or more metals selected from Zn, Co, Fe, Cr, Mn, and Ti.

Conventional Examples of Cu Alloys

Japanese Patent No. 1549371 (Japanese Patent Application No. Sho 57-6061) describes the use of a copper alloy as a material for lead wires used in various semiconductor instruments. Aside from Cu to serve as the major component, the copper alloy described in this patent contains 0.4 to 4wt% of Ni and 0.1 to 1wt% of Si. It also contains P and As as minor components.

Japanese Patent No. 1914484 (Japanese Patent Application No. Sho 58-65265) describes particular Cu alloys, each containing Cu as the major component. Among the Cu alloys described are one containing 0.01 to 2.0wt% of Cr, one containing 0.005 to 1.0wt% of Zr, and one containing both Cr and Zr.

Also, Japanese Patent No. 2136017 (Japanese Patent Application No. Sho 62-124365) describes one example of copper alloys for use in semiconductors. The copper alloy described in this patent contains 1.0 to 4.0wt% of Ni, 0.2 to 1.0wt% of

Si, 0.0005 to 0.5% of Ag, and 2.0wt% or less of Zn, Mn, Co and/or other metals.

Conventional Examples of the Use of Copper in Electrodes for Displays

5 Japanese Patent No. 2579106 (Japanese Patent Laid-Open Publication No. Hei 05-188401) mentions a Cr/Cu/Cr three-layered structure of gate electrodes for TFT (thin-film) transistors used in TFT-LCD panels. In addition, Japanese Patent Laid-Open Publication No. Hei 10-153788 mentions a
10 construction of gate electrodes for use in liquid crystal displays. This gate electrode consists of an alloy of Cu and Zr, and a ZrO oxide layer disposed over the alloy. Furthermore, Japanese Patent Laid-Open Publication No. 2001-196371 mentions a layered structure of conductive metals comprising copper
15 thin film patterns and IZO thin film patterns. Moreover, Japanese Patent Laid-Open Publication No. 2001-223217 describes a thin film of a metal oxide conductor having a contact resistance with a copper thin film of $1.0 \times 10^{-6} \Omega \cdot \text{cm}$ or less.

20

DISCLOSURE OF THE INVENTION

As described above, formation of the three-layered wiring requires sandwiching the aluminum electrode, which involves complex processes of initial deposition of Mo or Ti, followed
25 by deposition of aluminum-based metal, and then another

deposition of Mo or Ti.

As described above, examples of metals other than aluminum having low electrical resistance include Ag and Cu. Thus, attempts have been made to address the aforementioned problems by using Ag and Cu electrodes. Ag and Cu, however, have poor adhesion to glass substrates and silicon films and readily come off during the production process.

The present invention has been made in view of the above-described problems with a principal objective of providing a wiring material using a particular alloy that contains Ag as a major component (*i.e.*, Ag alloy) and offers improved adhesion to glass substrates and silicon films.

It is a second objective of the present invention to provide a wiring material using a particular alloy that contains Cu as a major component (*i.e.*, Cu alloy) and offers improved adhesion to glass substrates and silicon films.

1. The invention regarding Ag alloy

In an effort to find a way to address the aforementioned problems, the present inventors have found that these problems can be overcome by using a wiring made of an Ag alloy that contains Ag and Zr as essential components and further contains at least one metal selected from the group consisting of Au, Ni, Co and Al.

It has proven that such an Ag alloy wiring shows a good adhesion to glass substrates, has a low electrical resistance,

and allows little or no metal atoms to diffuse into the silicon layer even when the wiring comes into direct contact with the silicon layer. This Ag alloy wiring thus causes little or no decrease in the performance of the components of a TFT array.

It has also proven that even when an electrode (transparent electrode) for driving liquid crystal displays that contains indium oxide, tin oxide, or zinc oxide as a major component is formed directly over the Ag alloy metal electrode, the contact resistance between the metal electrode and the transparent electrode will not become excessively large and the device will operate stably.

The Ag alloy is preferably deposited by sputtering.

The target used contains Ag and Zr as essential components. Specifically, the target has a composition adjusted in such a manner that the resulting thin film contains 60 to 99wt% of Ag, 1 to 5wt% of Zr, 0 to 20wt% of each of Au, Ni and Co, and 0 to 39% of Al. In general, the target used in the sputtering has the same composition as the desired film. In this manner, the resulting film has a desired composition.

By adjusting the composition, compounds such as AgZr_2 and AgZr are produced. As a result, the dispersibility of Zr is improved, leading to generation of NiZr , NiZr_2 and Ni_3Zr , and AuZr_2 and Au_2Zr . This facilitates the dispersion of the third

component to ensure stable sputtering.

The Ag alloy metal electrode has a high adhesion to glass substrates and silicon films, does not come off during the production process, and can thus be manufactured in a stable manner.

Specific constructions of this aspect of the present invention are as follows:

1-A The invention regarding the wiring material

Intended to overcome the above-described problems, the present invention provides a wiring material made of an Ag alloy that contains Ag and Zr as essential components and further contains at least one metal selected from the group consisting of Au, Ni, Co, and Al. Such an Ag alloy shows an improved adhesion to glass substrates and silicon wafers.

Also, the present invention is the wiring material, wherein the above-described Ag alloy contains 60 to 99wt% of Ag and 1 to 5wt% of Zr.

If the amount of Zr is 1wt% or less, then the desired effect is not obtained and the adhesion strength to a silicon wafer remains low. In comparison, if Zr is present in excessive amounts, then the resistance (specific resistance) of the film made of the wiring material becomes large, sometimes exceeding $4 \mu\Omega \cdot \text{cm}$, and an increased occurrence of abnormal discharge is observed during sputtering. Thus, if present in any amount outside the range of 1 to 5wt%, Zr may

impart to the wiring material undesired properties for low resistance wirings.

The Ag alloy described in the first paragraph of this section for use in the wiring material preferably contains 60
5 to 99wt% of Ag, 1 to 5wt% of Zr, 0 to 20wt% of Au, 0 to 20wt% of Ni, 0 to 20wt% of Co, and 0 to 39wt% of Al.

It was observed that the addition of Au, Ni, and Co increases the strength of the adhesion to a glass surface. Nonetheless, if any of these components are present in amounts
10 exceeding 20wt%, the consequences will be an increase in cost for Au, and an increased resistance (specific resistance) greater than $4 \mu\Omega \cdot \text{cm}$ and an increased occurrence of abnormal discharge during sputtering for Ni. Thus, if present in any amount exceeding 20wt%, each of Au, Ni and Co may impart to
15 the wiring material undesired properties for low resistance wirings.

While Au, Ni, and Co have been described, it should be appreciated that each of these third metals must be of the type that does not diffuse into the semiconductor layer or of
20 the type that does not affect the performance of the semiconductor devices even when it diffuses into the semiconductor layer, or each must be added in amounts that do not affect the performance of the semiconductor devices.

Examples of the Ag/Zr alloys include AgZr_2 and AgZr .
25 Examples of the Zr/Ni alloys include NiZr , NiZr_2 , and Ni_3Zr .

Examples of the Zr/Au alloys include AuZr₂, Au₂Zr, AuZr₃, and Au₄Zr.

The wiring material according to the present invention may further contain 0 to 1wt% of at least one metal selected
5 from the group consisting of Re, Ru, Pd, and Ir.

The wiring material according to the present invention preferably has a specific resistance of 4 $\mu\Omega\cdot\text{cm}$ or less.

When used in thin films to serve as wirings of semiconductor devices, the material with 4 $\mu\Omega\cdot\text{cm}$ or a larger
10 specific resistance will cause delayed signals of non-negligible magnitude. Thus, it is preferred to obtain, by using wiring materials with 4 $\mu\Omega\cdot\text{cm}$ or smaller specific resistance, thin films for wirings that cause less delayed signals.

15 1-B The invention regarding the wiring boards

The present invention also provides a wiring board comprising a substrate, and wirings formed on the substrate and made of the wiring material having the above-described composition.

20 According to the present invention, the substrate used in the wiring board is preferably a glass substrate or a silicon substrate. As described, the wiring material of the present invention has strong adhesion to glass substrates and silicon wafers and can thus be used to make wirings that do not
25 readily come off the substrate.

When tested for the adhesion strength of the wiring to the substrate, the wiring board according to the present invention gives an adhesion of 3N or higher. If this adhesion is lower than 3N, the wiring may come off the substrate during the production process.

Preferably, the wirings of the wiring board according to the present invention are formed on a substrate as a gate wiring or a gate electrode of a thin film transistor. In such a case, the present invention serves as "semiconductor device wiring board." Such constructions make it possible to minimize the resistance of the gate electrodes of thin film transistors and thus helps improve the performance of thin film transistors.

The wirings of the wiring board according to the present invention are preferably formed on a substrate as a source wiring and a drain wiring or a source electrode and a drain electrode of thin film transistors. Also in this case, the present invention serves as a semiconductor device wiring board. This construction makes it possible to minimize the resistance of the source and gate electrodes of thin film transistors and thus helps improve the performance of thin film transistors.

Preferably, the wiring board of the present invention is non-conductive at least on its surface and includes a conductive metal oxide layer deposited over the wirings.

Preferably, the wirings and the metal oxide layer of the wiring board of the present invention form a stacked wiring of a two-layered structure.

The conductive metal oxide film for use in the present invention may be a transparent electrode such as IZO (registered trademark).

Such a construction can be used to minimize the resistance of electrodes of reflective LCDs or organic EL devices and helps improve the performance of thin film transistors and, thus, the performance of reflective LCDs and organic EL devices.

According to the present invention, the conductive metal oxide film may comprise an amorphous transparent conductive film that is formed of indium oxide and zinc oxide and has an atomic composition such that the following relationship holds: $\text{In}/(\text{In}+\text{Zn}) = 0.8 \text{ to } 0.95$. If this value is less than 0.8, then the resistance of the metal oxide thin film may become excessively large, whereas if the value is greater than 0.95, the etching rate may be decreased.

According to the present invention, the amorphous transparent conductive film has a work function of 5.4 eV or larger. When the wiring board of the present invention is used to construct an organic EL device, work functions of 5.4 eV or larger are preferred in order to enhance hole injection.

2. The invention regarding Cu alloys

In an effort to find a way to address the aforementioned problems, the present inventors have found that these problems can be overcome by using a particular Cu alloy in the wirings. Specifically, this Cu alloy contains Cu, the major component, in an amount of 80 to 99.5% and further contains Au and Co in a total amount of 0.5 to 20wt%.

It has proven that this Cu alloy wiring has high adhesion to glass substrates, has a low resistance, and hardly diffuses into the silicon layer even when the wiring comes in direct contact with the silicone layer. This Cu alloy wiring thus causes little or no decrease in the performance of the components of a TFT array.

It has also proven that even when an electrode (transparent electrode) for driving liquid crystal displays that contains indium oxide, tin oxide, or zinc oxide as a major component is formed directly over the Cu alloy metal electrode, the contact resistance between the metal electrode and the transparent electrode will not become excessively large and the device can operate stably.

The Cu alloy is preferably deposited by sputtering.

The target used contains Au and/or Co and contains Cu as the major component. Specifically, the target has a composition adjusted in such a manner that the resulting film contains 80 to 99.5wt% of Cu and 0.5 to 20wt% of Au and/or Co.

In general, the target used in the sputtering has the same

composition as the desired film. In this manner, the resulting film has a desired composition.

The target made of such compounds as CuAu and Cu₃Au facilitates not only the dispersion of Cu, but also the dispersion of the other components. As a result, the sputtering process is stabilized.

This Cu alloy metal electrode has high adhesion to glass substrates and silicon films, does not come off during the production process, and can thus be manufactured in a stable manner.

Specific constructions of this aspect of the present invention will now be described, starting from the invention regarding the wiring material.

2-A The invention regarding the wiring material

Intended to overcome the above-described problems, the present invention provides a wiring material made of a Cu alloy that is composed of Cu, along with Au and/or Co, and contains Cu in an amount of 80 to 99.5wt% and Au and/or Cu in a total amount of 0.5 to 20wt%.

Such a Cu alloy shows an improved adhesion to glass substrates and silicon wafers.

More preferably, the wiring material contains 0 to 10wt% of Au and 0 to 10wt% of Co.

Experiments conducted by the present inventors revealed the following facts concerning the amounts of Au and Co: Au

and Co cannot provide the desired effects if the total amount of the two components is 0.5% or less. In such a case, the wiring material has low adhesion to a glass surface.

Also, if the total amount of these components exceeds 20wt%, the consequences will be an increase in cost (for Au), and an increased resistance (specific resistance) and an increased occurrence of abnormal discharge during sputtering (for Co). Thus, if present in a total amount of greater than 20wt%, Au and Co may impart to the wiring material undesired properties for low resistance wirings.

While Au and Co have been described, it should be appreciated that each of these third metals must be of the type that does not diffuse into the semiconductor layer or of the type that does not affect the performance of the semiconductor devices even when it diffuses into the semiconductor layer, or each must be added in amounts that does not affect the performance of the semiconductor devices.

The wiring material according to the present invention preferably has a specific resistance of $4 \mu\Omega \cdot \text{cm}$ or less.

When used in thin film to serve as wirings of semiconductor devices, the material with $4 \mu\Omega \cdot \text{cm}$ or larger specific resistance will cause delayed signals of non-negligible magnitude. Thus, it is preferred to obtain, by using wiring materials with $4 \mu\Omega \cdot \text{cm}$ or smaller specific resistance, thin films for wirings that cause less delayed

signals.

The invention regarding a wiring board using the above-described wiring material will now be described.

2-B The invention regarding the wiring boards

5 The present invention also provides a wiring board comprising wirings formed of the above-described wiring material, a conductive metal oxide film, and a substrate. Preferably, the wirings and the metal oxide layer in the present invention form a stacked wiring of a two-layered
10 structure.

The conductive metal oxide film for use in the present invention may be a transparent electrode such as IZO, which is a registered trademark.

Such a construction can be used to minimize the
15 resistance of electrodes of reflective LCDs or organic EL devices and helps improve the performance of thin film transistors and, thus, the performance of reflective LCDs and organic EL devices.

Preferably, the wiring board of the present invention
20 contains at least one metal selected from the group consisting of Ru, Pd, Re, and Ir. This metal is contained in an amount of 0.05 atomic percent to 5 atomic percent.

When contained in amounts less than 0.05 atomic percent, the metal may not provide the desired effects and its work
25 function may not reach 5.4 eV. In comparison, the metal

present in amounts greater than 5 atomic percent may result in a decreased etchability and may cause unexpected coloring.

While the preferred range is specified as 0.05 to 5 atomic percent in the present invention, it is more preferred that the metal is contained in an amount of approximately 3 atomic percent: an example will be described later in which 3 atomic percent of the metal is contained.

According to the present invention, the conductive metal oxide film may comprise an amorphous transparent conductive film that is formed of indium oxide and zinc oxide and has an atomic composition such that the following relationship holds: $\text{In}/(\text{In}+\text{Zn}) = 0.8 \text{ to } 0.95$. If this value is less than 0.8, then the resistance of the metal oxide thin film may become excessively large, whereas if the value is greater than 0.95, the etching rate may be decreased.

Preferably, the substrate for use in the wiring board of the present invention is non-conductive on its surface.

Preferably, the wiring board according to the present invention comprises a wiring formed on the substrate and a thin film transistor.

Such constructions make it possible to minimize the resistance of the electrodes and wirings of thin film transistors and thus helps improve the performance of thin film transistors.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a table showing different properties of wiring materials according to the present embodiment.

Fig. 2 is a table showing different properties of wiring materials of the present embodiment.

Fig. 3 is a schematic cross-section of a transmissive TFT-LCD.

Fig. 4 is a schematic plan view showing the basic structure of a single pixel of a transmissive TFT-LCD.

Fig. 5 is a schematic cross-section taken along the line V-V' of Fig. 4.

BEST MODE FOR CARRYING OUT THE INVENTION

Preferred embodiments of the present invention will now be described with reference to the accompanying drawings.

1. An embodiment of Ag alloy

In this embodiment, an Ag alloy is proposed to serve as a wiring material according to the present invention. This alloy contains Ag as the major component and shows good adhesion to glass substrates and silicon wafers.

In particular, one example is described in which such an alloy is produced by sputtering. First, we briefly describe the preparation of a target used in the sputtering process. At a predetermined ratio, Zr, along with Ni, Mo, or Au, is mixed with Ag and melted in a vacuum smelting furnace. The melt is

allowed to cool and harden and the hardened alloy is rolled into a plate, which in turn is cut and abraded to form a target measuring 4 inches in diameter. For sputtering, the target is mounted on a backing plate of a sputtering apparatus.

5 By the time the sputtering process using this target is finished, a film has been deposited on a glass surface or a silicon wafer. The performances of thin films having different compositions are compared with one another. The results of the comparison are shown in the table in Fig. 1, which contains
10 the compositions used, conductivities of the thin films and other data.

The composition of each film was determined by an X-ray microanalyzer (EPMA: Electron Probe Micro-Analysis), and the conductivity of each film was determined by the four probe
15 technique.

Each film was measured for the peel strength in the scratch test and tape peel test. The apparatus used for the scratch test was Micro-Scratch Tester (CSME). The peel strength was determined under the following conditions.

20 Scratch distance: 20 mm

Scratch load: 0 to 10 N

Load rate: 10 N/min

Scratch speed: 20 mm/min

Shape of diamond cone: 200 μ m in diameter

25 After the scratch test using the above conditions, the

sample was observed with a light microscope and the distance between the point where the glass substrate (wafer) or silicon was exposed (peel point) and the starting point of scratching was measured to determine the peel load.

5 In the tape peel test, a 1mm-pitch grid is cut on the thin film with a knife, and a strip of an adhesive tape is applied to the film. The tape is then peeled and the degree of peeling of the film is determined as a measure of adhesion.

 The scratch test and the tape peel test were performed
10 according to standards defined by Japanese Industrial Standards (JIS).

 The table in Fig. 1 shows six examples in which different alloys, formed by adding Zr, Au, Co, Ni, and other metals to Ag, were used as the target in sputtering to deposit a film on
15 a glass substrate and a silicon wafer.

 In Example 1-2, Co was added to (Ag + Zr) to form the target. In Example 1-3, Ni was added to (Ag + Zr), while Al is added to (Ag + Zr) in Example 1-4. In Example 1-5, Pd was added to the composition where Au was added to (Ag + Zr) shown
20 in Example 1-1. In Example 1-6, Ru was added to the composition where Au was added to (Ag + Zr) shown in Example 1-1.

 In each example, the adhesion strength of 3 N or greater was achieved. In each example, no peeling was observed on the
25 glass substrate or silicon wafer in the tape peel test.

In Comparative Example 1-1, Ag was used alone. In this example, the adhesion strength was 1 N or less and peeling was observed on each of the glass substrate and the silicon wafer.

Comparative Examples 1-2 through 1-8 did not use Zr.

5 Peeling was observed on the glass substrate and the silicon wafer in each of these examples.

Comparative Example 1-9, in which Pd was added to Comparative Example 1-2, showed a large specific resistance and thus did not achieve the objective of the invention. In
10 addition, peeling was observed on the glass substrate.

[Example 1-1]

This example is for reference and comprises a transmissive TFT-LCD in which an exemplary Ag alloy of the present invention is used in the wiring. While the basic
15 structure of transmissive TFT-LCD has already been described with reference to Figs. 3 to 5, various protective films/layers (not shown in Figs. 3 to 5) are formed in actual
production processes.

First, an Ag alloy containing 1.7wt% Zr and 3.5wt% Au is
20 deposited on a transparent glass substrate 18b to a film thickness of 1500 angstroms (specific resistance = $2.8 \mu\Omega \cdot \text{cm}$) by using the high frequency sputtering technique. The process is performed at room temperature. The resulting film is subjected to a photo-etching process using an aqueous etching
25 solution containing nitric acid, acetic acid, and phosphoric

acid to form a gate electrode 34 and wirings for the gate electrode of desired shape.

Next, using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the gate insulation film is deposited to a film thickness of 3000 angstroms. This is followed by the deposition of $\alpha\text{-Si:H(i)}$ film 38 to a film thickness of 3500 angstroms. As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas and an $\text{SiH}_4\text{-N}_2$ -based mixed gas are used for the deposition of the SiN_x film 35 and the $\alpha\text{-Si:H(i)}$ film 38, respectively. The SiN_x film 35 is subjected to dry etching using CF_4 gas to form a desired protective layer for the channels.

Using an $\text{SiH}_4\text{-H}_2\text{-PH}_3$ -based mixed gas, an $\alpha\text{-Si:H(n)}$ film is then deposited to a film thickness of 3000 angstroms. Subsequently, an Ag alloy containing 1.7wt% Zr and 1.7wt% Ni is deposited over the $\alpha\text{-Si:H(n)}$ film to a film thickness of 0.3 μm (specific resistance = 3.4 $\mu\Omega\cdot\text{cm}$) using the sputtering technique. The process is performed at room temperature.

This layer is then subjected to a photo-etching process using an aqueous etching solution containing nitric acid, acetic acid, and phosphoric acid to form a desired pattern of a source electrode 32 and a drain electrode 36. Subsequently, the $\alpha\text{-Si:H(i)}$ film 38 and the $\alpha\text{-Si:H(n)}$ film are each etched into a desired pattern using dry etching with CF_4 gas in conjunction with wet etching with an aqueous solution of

hydrazine ($\text{NH}_2\text{NH}_2 \cdot \text{H}_2\text{O}$). Using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the gate insulation film is then deposited to a film thickness of 3000 angstroms.

As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas is used for the

5 deposition of the SiN_x film. The SiN_x film is then subjected to a photo-etching process by dry etching using CF_4 gas to form an output port for the gate electrode 34, an output port for the source electrode 32, and a through hole 40b to provide electrical connection between the drain electrode 36 and the
10 transparent electrode 20b. The Ag alloy electrode so obtained is then exposed to argon plasma to clean the surface.

Subsequently, an amorphous transparent conductive film composed mainly of indium oxide and zinc oxide is deposited using the sputtering technique. The target used for the

15 sputtering process is a sintered body of $\text{In}_2\text{O}_3\text{-ZnO}$ in which the atomic ratio of $\text{In}/(\text{In}+\text{Zn})$ has been adjusted to 0.83. This sintered body is mounted on the cathode of a planar magnetron sputtering apparatus so that it can serve as the target. Using a pure argon gas or an argon gas containing approximately
20 1vol% oxygen as the discharge gas, a film for transparent electrode 20b is deposited to a film thickness of 1200 angstroms. The X-ray diffraction analysis of the resulting $\text{In}_2\text{O}_3\text{-ZnO}$ film showed no peaks, indicating that the film was amorphous.

25 The resulting film for transparent electrode 20b was

subjected to a photo-etching process using a 3.4wt% aqueous solution of oxalic acid to form a desired pattern for pixel electrodes and output electrodes. A black matrix pattern is then formed to complete an α -SiTFT substrate 14. This TFT substrate 14 was used to make a TFT-LCD flat display. Video signals were provided to the display to confirm that the display had good performance.

[Example 1-2]

This example comprises a reflective TFT-LCD in which an exemplary Ag alloy of the present invention is used in the wiring. The basic structure of reflective TFT-LCD is different from that of the transmissive TFT-LCD in that a light reflective electrode is used in place of the transparent electrode 20b on the TFT substrate 14 of the transmissive TFT-LCD. While not shown in Figs. 3 to 5, various protective films/layers are deposited in actual production processes. It is well known that reflective TFT-LCDs are different from transmissive TFT-LCDs in many ways, aside from the electrodes.

First, an Ag alloy containing 1.7wt% Zr and 3.5wt% Au is deposited on a transparent glass substrate 18b to a film thickness of 1500 angstroms (specific resistance = $2.8 \mu\Omega \cdot \text{cm}$) by using the high frequency sputtering technique. The process is performed at room temperature. The resulting film is subjected to a photo-etching process using an aqueous etching solution containing nitric acid, acetic acid, and phosphoric

acid to form a gate electrode 34 and wirings for the gate electrode of desired shape.

Next, using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the gate insulation film is deposited to a film thickness of 3000 angstroms. This is followed by the deposition of $\alpha\text{-Si:H(i)}$ film 38 to a film thickness of 3500 angstroms. As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas and an $\text{SiH}_4\text{-N}_2$ -based mixed gas are used for the deposition of the SiN_x film 35 and the $\alpha\text{-Si:H(i)}$ film 38, respectively. The SiN_x film 35 is subjected to dry etching using CF_4 gas to form a desired protective layer for the channels.

Using an $\text{SiH}_4\text{-H}_2\text{-PH}_3$ -based mixed gas, an $\alpha\text{-Si:H(n)}$ film is then deposited to a film thickness of 3000 angstroms. Subsequently, an Ag alloy containing 1.7wt% Zr and 1.7wt% Ni is deposited over the $\alpha\text{-Si:H(n)}$ film to a film thickness of 0.3 μm (specific resistance = 3.4 $\mu\Omega\cdot\text{cm}$) using the sputtering technique. The process is performed at room temperature.

Subsequently, an amorphous transparent conductive film composed mainly of indium oxide and zinc oxide is deposited using the sputtering technique.

This layer is then subjected to a photo-etching process using an aqueous etching solution containing nitric acid, acetic acid, and phosphoric acid to form a desired pattern of a source electrode 32 and a drain electrode 36. Subsequently,

the α -Si:H(i) film 38 and the α -Si:H(n) film are each etched into a desired pattern using dry etching with CF_4 gas in conjunction with wet etching with hydrazine ($\text{NH}_2\text{NH}_2 \cdot \text{H}_2\text{O}$). Using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the gate insulation film is then deposited to a film thickness of 3000 angstroms. As the discharge gas, an SiH_4 - NH_3 - N_2 gas is used for the deposition of the SiN_x film. The SiN_x film is then subjected to a photo-etching process by dry etching using CF_4 gas to form an output port for the gate electrode 34, an output port for the source electrode 32, and a through hole 40b to provide electrical connection between the drain electrode 36 and the transparent electrode 20b. The Ag alloy electrode so obtained is then exposed to argon plasma to clean the surface.

Subsequently, an Ag alloy containing 1.7wt% Zr and 3.5wt% Au is deposited to a film thickness of $0.2 \mu\text{m}$ (specific resistance = $2.8 \mu\Omega \cdot \text{cm}$) using the sputtering technique. The process is performed at room temperature.

Subsequently, an amorphous transparent conductive film composed mainly of indium oxide and zinc oxide is deposited using the sputtering technique. The target used for the sputtering process is a sintered body of In_2O_3 - ZnO in which the atomic ratio of $\text{In}/(\text{In}+\text{Zn})$ has been adjusted to 0.83. This sintered body is mounted on the cathode of a planar magnetron sputtering apparatus so that it can serve as the target. Using

a pure argon gas or an argon gas containing approximately 1vol% oxygen as the discharge gas, a film for transparent electrode 20b is deposited to a film thickness of 1200 angstroms. The X-ray diffraction analysis of the resulting
5 $\text{In}_2\text{O}_3\text{-ZnO}$ film showed no peaks, indicating that the film was amorphous.

To form a desired pattern for reflective pixel electrodes and output electrodes, the resulting film for transparent electrode 20b was subjected to an aqueous etching solution
10 containing nitric acid, acetic acid, and phosphoric acid, which had had its concentration adjusted so that it could etch the Ag alloy layer and the indium oxide-zinc oxide layer at once.

A black matrix pattern is then formed to complete an α -
15 SiTFT substrate 14. This TFT substrate 14 was used to make a TFT-LCD flat display. Video signals were provided to the display to confirm that the display had good performance.

[Example 1-3]

This example is for reference and comprises a substrate
20 for organic EL device in which an exemplary Ag alloy of the present invention is used in the wiring.

A conductive metal oxide film was deposited in the same manner as in Example 1-1. The film was deposited to a thickness of 300 angstroms using the sputtering technique with
25 a target made of $\text{In}_2\text{O}_3\text{-ZnO}$. The atomic ratio of $\text{In}/(\text{In}+\text{Zn})$ had

been adjusted to 0.83. Thus, this conductive metal oxide film corresponds to the transparent electrode described in Example 1-1.

Example 1-3 is characteristic in that the composition of the conductive metal oxide film contains Pd in an amount of 3 atomic % with respect to the total amount of metals. The work function of this conductive film was determined, by an atmospheric-ultraviolet photoelectron spectrometer (AC-1, Riken Keiki Co., Ltd.), to be 5.65 eV, indicating that the conductive film had desirable properties for use as an anode of an organic EL device.

While Pd was used in this example, Ru, Re, and Ir may also be used. When used, these metals gave work functions of 5.51 eV, 5.63 eV and 5.61 eV, respectively. Thus, each proved to have desirable properties for use as an anode of an organic EL device.

2. An embodiment of Cu alloy

In this embodiment, a Cu alloy is proposed to serve as a wiring material according to the present invention. This alloy contains Cu as the major component and shows good adhesion to glass substrates and silicon wafers.

In particular, one example is described in which such an alloy is produced by sputtering. First, we briefly describe the preparation of a target used in the sputtering process. At a predetermined ratio, Au and/or Co is mixed with Cu and

melted in a vacuum smelting furnace. The melt is allowed to cool and harden and the hardened alloy is rolled into a plate, which in turn is cut and abraded to form a target measuring 4 inches in diameter. For sputtering, the target is mounted on a backing plate of a sputtering apparatus. By the time the sputtering process using this target is finished, a film has been deposited on a glass surface or a silicon wafer.

The performances of thin films having different compositions are compared with one another. The results of the comparison are shown in the table in Fig. 2. The table contains the compositions of the targets used, film thicknesses, measured resistances, specific resistances, adhesion strengths, the results of the tape peel test and other data. Each film was deposited at room temperature.

The composition of each film was determined by an X-ray microanalyzer (EPMA: Electron Probe Micro-analysis), and the conductivity (measured resistance and specific resistance) of each film was determined by the four probe technique.

The peel strength of each film was determined using a similar technique and conditions to those used in the above-described embodiment of Ag alloy.

Each film was tested in the tape peel test using a similar technique and conditions to those used in the above-described embodiment of Ag alloy. The table in Fig. 2 shows the number of 1mmx1mm tape pieces out of 100 that came off.

The scratch test and the tape peel test were performed according to standards defined by Japanese Industrial Standards (JIS).

[Basic Examples]

5 The table in Fig. 2 shows total of six examples: examples in which the target was composed of Cu with Au added; examples in which the target was composed of Cu with Co added; and examples in which the target was composed of Cu with Au and Co both added. In each example, one of the above-described alloys
10 was used as the target that was subjected to sputtering to deposit a film on a glass substrate or a silicon wafer.

In Examples 2-1 and 2-2, the target for forming the thin film was composed of Cu with Au added. The targets of Examples 2-1 and 2-2 contained Au in amounts of 4.0wt% and 1.7%,
15 respectively.

In Example 2-1, the specific resistance was determined to be $3.8 \mu\Omega \cdot \text{cm}$. The adhesion strength was 5.72 N for the glass substrate and 3.48 N for the silicon wafer. The results of the tape peel test indicate that no peeling was observed for the
20 glass substrate and only two out of 100 tape pieces came off the silicon wafer.

In Example 2-2, the specific resistance was determined to be $2.9 \mu\Omega \cdot \text{cm}$. The adhesion strength was 4.37 N for the glass substrate and 3.12 N for the silicon wafer. The results of the
25 tape peel test indicate that no peeling was observed for the

glass substrate and only five out of 100 tape pieces came off the silicon wafer.

In Examples 2-3 and 2-4, the Cu target for forming the thin film contained Co. Specifically, the targets of Examples 2-3 and 2-4 contained Co in amounts of 3.7wt% and 4.8%, respectively.

In Example 2-3, the specific resistance was determined to be $2.9 \mu\Omega \cdot \text{cm}$. The adhesion strength was 5.54 N for the glass substrate and 3.65 N for the silicon wafer. The results of the tape peel test indicate that no peeling was observed for the glass substrate and ten out of 100 tape pieces came off the silicon wafer.

In Example 2-4, the specific resistance was determined to be $3.2 \mu\Omega \cdot \text{cm}$. The adhesion strength was 5.68 N for the glass substrate and 3.68 N for the silicon wafer. The results of the tape peel test indicate that no peeling was observed for the glass substrate and ten out of 100 tape pieces came off the silicon wafer.

In Examples 2-5 and 2-6, the Cu target for forming the thin film contained Au and Co. Specifically, the target of Example 2-5 contained Au and Co in amounts of 2.3wt% and 2.7%, respectively. The target of Example 2-6 contained Au and Co in amounts of 1.2% and 4.2%, respectively.

In Example 2-5, the specific resistance was determined to be $3.9 \mu\Omega \cdot \text{cm}$. The adhesion strength was 5.52 N for the glass

substrate and 3.54 N for the silicon wafer. The results of the tape peel test indicate that no peeling was observed in the glass substrate or in the silicon wafer.

In Example 2-6, the specific resistance was determined to be 4.0 $\mu\Omega\cdot\text{cm}$. The adhesion strength was 5.31 N for the glass substrate and 3.07 N for the silicon wafer. The results of the tape peel test indicate that no peeling was observed in the glass substrate or in the silicon wafer.

[Comparative Examples]

The table of Fig. 2 also contains Comparative Examples 2-1 through 2-9 for comparison with Basic Examples described above.

Comparative Example 2-1 was composed only of Cu. In this Comparative Example 1, the specific resistance was determined to be 4.0 $\mu\Omega\cdot\text{cm}$. The adhesion strength was 0.1 N or less for each of the glass substrate and the silicon wafer. The results of the tape peel test indicate that all of the one hundred tape pieces came off in each of the glass substrate and the silicon wafer.

In Comparative Example 2-2, the Cu target for forming the thin film contained 3.0wt% Zr. In this Comparative Example 2-2, the specific resistance was determined to be 10.1 $\mu\Omega\cdot\text{cm}$. The adhesion strength was 0.65 N for the glass substrate and 1.64 N for the silicon wafer. The results of the tape peel test indicate that twelve out of 100 tape pieces came off the glass

substrate and 40 pieces came off the silicon wafer.

In Comparative Example 2-3, the Cu target for forming the thin film contained 1.9wt% Ni. In this Comparative Example 2-3, the specific resistance was determined to be $8.9 \mu\Omega\cdot\text{cm}$. The adhesion strength was 0.24 N for the glass substrate and 1.41 N for the silicon wafer. The results of the tape peel test indicate that all of the one hundred tape pieces came off the glass substrate and 30 pieces came off the silicon wafer.

In Comparative Example 2-4, the Cu target for forming the thin film contained 5.4wt% Al. In this Comparative Example 2-4, the specific resistance was determined to be $11.1 \mu\Omega\cdot\text{cm}$. The adhesion strength was 0.13 N for the glass substrate and 1.71 N for the silicon wafer. The results of the tape peel test indicate that all of the one hundred tape pieces came off the glass substrate and 50 pieces came off the silicon wafer.

In Comparative Example 2-5, the Cu target for forming the thin film contained 6.5wt% In. In this Comparative Example 2-5, the specific resistance was determined to be $9.0 \mu\Omega\cdot\text{cm}$. The adhesion strength was 0.73 N for the glass substrate and 0.82 N for the silicon wafer. The results of the tape peel test indicate that 20 out of 100 tape pieces came off the glass substrate and 30 pieces came off the silicon wafer.

In Comparative Example 2-6, the Cu target for forming the thin film contained 2.8wt% Bi. In this Comparative Example 2-6, the specific resistance was determined to be $10.2 \mu\Omega\cdot\text{cm}$. The

adhesion strength was 0.62 N for the glass substrate and 0.94 N for the silicon wafer. The results of the tape peel test indicate that all of the one hundred tape pieces came off in each of the glass substrate and the silicon wafer.

5 In Comparative Example 2-7, the Cu target for forming the thin film contained 1.7wt% Sn. In this Comparative Example 2-7, the specific resistance was determined to be $46.6 \mu\Omega\cdot\text{cm}$. The adhesion strength was 0.53 N for the glass substrate and 0.64 N for the silicon wafer. The results of the tape peel test
10 indicate that all of the one hundred tape pieces came off in each of the glass substrate and the silicon wafer.

 In Comparative Example 2-8, the Cu target for forming the thin film contained 1.2wt% Ti. In this Comparative Example 2-8, the specific resistance was determined to be $4.5 \mu\Omega\cdot\text{cm}$. The
15 adhesion strength was 0.47 N for the glass substrate and 0.78 N for the silicon wafer. The results of the tape peel test
indicate that all of the one hundred tape pieces came off in each of the glass substrate and the silicon wafer.

 In Comparative Example 2-9, the Cu target for forming the
20 thin film contained 1.6wt% W. In this Comparative Example 2-9, the specific resistance was determined to be $21.5 \mu\Omega\cdot\text{cm}$. The adhesion strength was 0.4d7 N for the glass substrate and 0.78 N for the silicon wafer. The results of the tape peel test
indicate that all of the one hundred tape pieces came off in
25 each of the glass substrate and the silicon wafer.

[Application Examples]

[Application Example 2-1]

This example is for reference and comprises a transmissive TFT-LCD in which an exemplary Cu alloy of the present invention is used in the wiring. While the basic structure of transmissive TFT-LCD has already been described with reference to Figs. 3 to 5, various protective films/layers (not shown in Figs. 3 to 5) are formed in actual production processes.

First, a Cu alloy containing 2.3wt% Au and 2.7wt% Co is deposited on a transparent glass substrate 18b to a film thickness of 1500 angstroms (specific resistance = $3.9 \mu\Omega \cdot \text{cm}$) by using the high frequency sputtering technique. The resulting film is subjected to a photo-etching process using an ammonium persulfate-based aqueous etching solution to form a gate electrode 34 and wirings for the gate electrode of desired shape.

Next, using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the gate insulation film is deposited to a film thickness of 3000 angstroms. This is followed by the deposition of $\alpha\text{-Si:H(i)}$ film 38 to a film thickness of 3500 angstroms. As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas and an $\text{SiH}_4\text{-N}_2$ -based mixed gas are used for the deposition of the SiN_x film 35 and the $\alpha\text{-Si:H(i)}$ film 38, respectively. The SiN_x film 35 is subjected to dry etching

using CF_4 gas to form a desired protective layer for the channels.

Using an $\text{SiH}_4\text{-H}_2\text{-PH}_3$ -based mixed gas, an $\alpha\text{-Si:H(n)}$ film is then deposited to a film thickness of 3000 angstroms.

5 Subsequently, a Cu alloy containing 1.2wt% Au and 4.2wt% Co is deposited over the $\alpha\text{-Si:H(n)}$ film to a film thickness of 0.3 μm (specific resistance = 4.0 $\mu\Omega\cdot\text{cm}$) using the sputtering technique. The process is performed at room temperature.

This layer is then subjected to a photo-etching process
10 using an aqueous etching solution containing hydrochloric acid, potassium hydrogen peroxysulfate, and hydrofluoric acid to form a desired pattern of a source electrode 32 and a drain electrode 36. Subsequently, the $\alpha\text{-Si:H(i)}$ film 38 and the $\alpha\text{-Si:H(n)}$ film are each etched into a desired pattern using dry
15 etching with CF_4 gas in conjunction with wet etching with an aqueous solution of hydrazine ($\text{NH}_2\text{NH}_2\cdot\text{H}_2\text{O}$). Using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the insulation film is then deposited thereover to a film thickness of 3000 angstroms. As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas is used for the deposition of the SiN_x film. The
20 SiN_x film is then subjected to a photo-etching process by dry etching using CF_4 gas to form an output port for the gate electrode 34, an output port for the source electrode 32, and a through hole 40b to provide electrical connection between
25 the drain electrode 36 and the transparent electrode 20b. The

Cu alloy electrode so obtained is then exposed to argon plasma to clean the surface.

Subsequently, an amorphous transparent conductive film composed mainly of indium oxide and zinc oxide is deposited using the sputtering technique. The target used for the sputtering process is a sintered body of $\text{In}_2\text{O}_3\text{-ZnO}$ in which the atomic ratio of $\text{In}/(\text{In}+\text{Zn})$ has been adjusted to 0.83. This sintered body is mounted on the cathode of a planar magnetron sputtering apparatus so that it can serve as the target. Using a pure argon gas or an argon gas containing approximately 1vol% oxygen as the discharge gas, a film for transparent electrode 20b is deposited to a film thickness of 1200 angstroms. The X-ray diffraction analysis of the resulting $\text{In}_2\text{O}_3\text{-ZnO}$ film showed no peaks, indicating that the film was amorphous.

The resulting film for transparent electrode 20b was subjected to a photo-etching process using a 3.4wt% aqueous solution of oxalic acid to form a desired pattern for pixel electrodes and output electrodes. A black matrix pattern is then formed to complete an $\alpha\text{-SiTFT}$ substrate 14. This TFT substrate 14 was used to make a TFT-LCD flat display. Video signals were provided to the display to confirm that the display had good performance.

[Application Example 2-2]

This example comprises a reflective TFT-LCD in which an

exemplary Cu alloy of the present invention is used in the wiring. The basic structure of reflective TFT-LCD is different from that of the transmissive TFT-LCD in that a light reflective electrode is used in place of the transparent electrode 20b on the TFT substrate 14 of the transmissive TFT-LCD. While not shown in Figs. 3 to 5, various protective films/layers are deposited in actual production processes. It is well known that reflective TFT-LCDs are different from transmissive TFT-LCDs in many ways, aside from the electrodes.

First, a Cu alloy containing 2.3wt% Au and 2.7wt% Co is deposited on a transparent glass substrate 18b to a film thickness of 1500 angstroms (specific resistance = $3.9 \mu\Omega \cdot \text{cm}$) by using the high frequency sputtering technique. The resulting film is subjected to a photo-etching process using an ammonium persulfate-based aqueous etching solution to form a gate electrode 34 and wirings for the gate electrode of desired shape.

Next, using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the gate insulation film is deposited to a film thickness of 3000 angstroms. This is followed by the deposition of $\alpha\text{-Si:H(i)}$ film 38 to a film thickness of 3500 angstroms. As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas and an $\text{SiH}_4\text{-N}_2$ -based mixed gas are used for the deposition of the SiN_x film 35 and the $\alpha\text{-Si:H(i)}$ film 38, respectively. The SiN_x film 35 is subjected to dry etching

using CF_4 gas to form a desired protective layer for the channels.

Using an $\text{SiH}_4\text{-H}_2\text{-PH}_3$ -based mixed gas, an $\alpha\text{-Si:H(n)}$ film is then deposited to a film thickness of 3000 angstroms.

5 Subsequently, a Cu alloy containing 1.2wt% Au and 4.2wt% Co is deposited over the $\alpha\text{-Si:H(n)}$ film to a film thickness of 0.3 μm (specific resistance = $4.0 \mu\Omega\cdot\text{cm}$) using the sputtering technique. The process is performed at room temperature.

This layer is then subjected to a photo-etching process
10 using an aqueous etching solution containing hydrochloric acid, potassium hydrogen peroxysulfate, and hydrofluoric acid to form a desired pattern of a source electrode 32 and a drain electrode 36. Subsequently, the $\alpha\text{-Si:H(i)}$ film 38 and the $\alpha\text{-Si:H(n)}$ film are each etched into a desired pattern using dry
15 etching with CF_4 gas in conjunction with wet etching with hydrazine ($\text{NH}_2\text{NH}_2\cdot\text{H}_2\text{O}$). Using the glow discharge CVD technique, a silicon nitride (SiN_x) film to serve as the insulation film is then deposited to a film thickness of 3000 angstroms. As the discharge gas, an $\text{SiH}_4\text{-NH}_3\text{-N}_2$ gas is used for the
20 deposition of the SiN_x film. The SiN_x film is then subjected to a photo-etching process by dry etching using CF_4 gas to form an output port for the gate electrode 34, an output port for the source electrode 32, and a through hole 40b to provide electrical connection between the drain electrode 36 and the
25 transparent electrode 20b. The Cu alloy electrode so obtained

is then exposed to argon plasma to clean the surface.

Subsequently, a Cu alloy containing 2.3wt% Au and 2.7wt% Co is deposited to a film thickness of 0.2 μm (specific resistance = 3.9 $\mu\Omega\cdot\text{cm}$) using the sputtering technique. The process is performed at room temperature.

An amorphous transparent conductive film composed mainly of indium oxide and zinc oxide is then deposited using the sputtering technique. The target used for the sputtering process is a sintered body of $\text{In}_2\text{O}_3\text{-ZnO}$ in which the atomic ratio of $\text{In}/(\text{In}+\text{Zn})$ has been adjusted to 0.83. This sintered body is mounted on the cathode of a planar magnetron sputtering apparatus so that it can serve as the target. Using a pure argon gas or an argon gas containing approximately 1vol% oxygen as the discharge gas, a film for transparent electrode 20b is deposited to a film thickness of 300 angstroms. The X-ray diffraction analysis of the resulting $\text{In}_2\text{O}_3\text{-ZnO}$ film showed no peaks, indicating that the film was amorphous.

To form a desired pattern for reflective pixel electrodes and output electrodes, the resulting film for transparent electrode 20b was subjected to a photo-etching process using an ammonium persulfate-based aqueous etching solution. This solution had had its concentration adjusted so that it could etch the Cu alloy layer and the indium oxide-zinc oxide layer at once.

A black matrix pattern is then formed to complete an α -SiTFT substrate 14. This TFT substrate 14 was used to make a TFT-LCD flat display. Video signals were provided to the display to confirm that the display had good performance.

5 [Application Example 2-3]

This example is for reference and comprises a substrate for organic EL device in which an exemplary Cu alloy of the present invention is used in the wiring.

First, a Cu alloy containing 2.3wt% Au and 2.7wt% Co was
10 deposited on a glass substrate to a film thickness of 1500 angstroms (specific resistance = $3.9 \mu\Omega \cdot \text{cm}$).

A conductive metal oxide film was then deposited over the Cu alloy film. The film was deposited to a thickness of 300 angstroms using the sputtering technique with a target made of
15 In_2O_3 -ZnO. The atomic ratio of In/(In+Zn) had been adjusted to 0.83. Thus, this conductive metal oxide film corresponds to the transparent electrode described in Examples 2-1 and 2-2.

The present Application Example 2-3 is characteristic in that the composition of the conductive metal oxide film
20 contains Pd in an amount of 3 atomic % with respect to the total amount of metals.

The work function of this conductive film was determined, by an atmospheric-ultraviolet photoelectron spectrometer (AC-1, Riken Keiki Co., Ltd.), to be 5.65 eV, indicating that the
25 conductive film had desirable properties for use as an anode

of an organic EL device.

While Pd was used in this example, Ru, Re, and Ir may also be used. When used, these metals gave work functions of 5.51 eV, 5.63 eV, and 5.61 eV, respectively. Thus, each proved
5 to have desirable properties for use as an anode of an organic EL device.

As set forth, the present invention provides a wiring material that shows an improved adhesion strength to glass substrates and silicon wafers while offering a low resistance.
10 Thus, when used in the wirings in TFT-LCDs, organic EL devices, or other electronic devices, the wiring material of the present invention prevents the peeling of the wirings and its low resistance helps improve properties of the devices.

The present invention, in which a particular Ag alloy or
15 Cu alloy is sputtered to form a film to serve as a metal electrode, also makes it possible to minimize the number of production steps involved and enables the efficient production of TFT arrays. Thus, the invention allows low cost production of TFT-LCDs and TFT-driven organic EL devices. In particular,
20 the present invention employs a particular composition that minimizes the occurrence of abnormal discharge during sputtering and thus enables efficient production of the devices.

CLAIMS

1. A wiring material comprising an Ag alloy that contains Ag and Zr as components and at least one metal selected from the group consisting of Au, Ni, Co and Al, wherein the Ag alloy
5 contains 96.6wt% or more of Ag.
2. The wiring material according to claim 1, wherein the Ag alloy according to claim 1 contains 96.6wt% to 99wt% of Ag and 1 to 5wt% of Zr.
3. The wiring material according to claim 1, wherein the Ag
10 alloy according to claim 1 contains 1 to 3.4wt% of Zr;
0 to 2.4wt% of Au;
0 to 2.4wt% of Al;
0 to 2.4wt% of Co; and
0 to 2.4wt% of Ni.
- 15 wherein sum of Au, Al, Co and Ni is not more than 2.4wt%.
4. The wiring material according to any one of claims 1 to 3, further containing 0 to 1wt% of at least one metal selected from the group consisting of Re, Ru, Pd, and Ir.
5. The wiring material formed of the Ag alloy according to
20 any one of claims 1 to 4, having a specific resistance of 4 $\mu\Omega\cdot\text{cm}$ or less.
6. A wiring board comprising:
a substrate; and
a wiring composed of the wiring material according to any
25 one of claims 1 to 4.
7. The wiring board according to claim 6, wherein the

substrate is a glass substrate or a silicon substrate.

8. The wiring board according to claim 6 or 7, wherein the adhesion strength of the wiring to the substrate as determined by the scratch method is 3 N or higher.

5 9. The wiring board for a semiconductor device according to any one of claims 6 to 8, wherein the wiring comprises a gate wiring and a gate electrode of a thin film transistor formed on the wiring board.

10 10. The wiring board for a semiconductor device according to any one of claims 6 to 8, wherein the wiring comprises a source wiring and a drain wiring, and a source electrode and a drain electrode, of a thin film transistor formed on the wiring board.

11. The wiring board according to any one of claims 6 to 10,
15 wherein: the substrate is non-conductive at least on its surface; and

a conductive metal oxide layer is deposited over the wiring.

12. The wiring board according to claim 11, wherein the
20 wiring and the conductive metal oxide film form a stacked wiring of a two-layered structure.

13. The wiring board according to claim 11 or 12, wherein the conductive metal oxide film comprises an amorphous transparent conductive film that is formed of indium oxide and zinc oxide
25 and has an atomic composition such that the following

relationship holds: $\text{In}/(\text{In}+\text{Zn}) = 0.8 \text{ to } 0.95$.

14. The wiring board according to any one of claims 11 to 13, wherein the amorphous transparent conductive film has a work function of 5.4 eV or larger.